

TQTHDB326V0

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Thyristors Solid Protection Device Bidirectional transient voltage suppressors

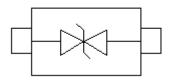
• Description

The TQTHDB326V0 is designed with TECH CHIP Punch-Through process TVS technology to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time provide best in class protection on designs that are exposed to ESD. Because of its small size, it is suited for use in cellular phones, MP3 players, digital cameras and many other portable applications where board space comes at a premium.Also because of its low capacitance, it is suited for use in high frequency designs such as USB 2.0 high speed, USB 3.0 super speed, VGA, DVI, HDMI, ESATA and other high speed line applications.

• Features

- For surface mounted applications to optimize board space
- Low profile package
- Bidirectional crowbar protection
- \blacktriangleright Low leakage current : I = 5uA max
- Low on-state voltage
- Low Capacitance
- $\blacktriangleright \quad \text{Response Time is} < 1 \text{us}$
- ➢ YD/T 950 IEC 61000-4-5
- Solid-state silicon technology
- Meets MSL 1 Requirements
- ROHS compliant
- TECH CHIP technology

PIN configuration



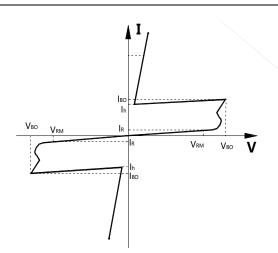




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• Electronic Parameter

Symbol	Parameter	
V _{RM}	Stand-off voltage	
V _{BR}	Breakdown voltage	
V _{BO}	Switching Voltage	
IBO	Breakover current	
I _{RM}	Leakage current at V_{RM}	
Ipp	Peak pulse current	
I _H	Holding current	
VT	On-state Voltage at I _T	
Co	Off-state Capacitance	



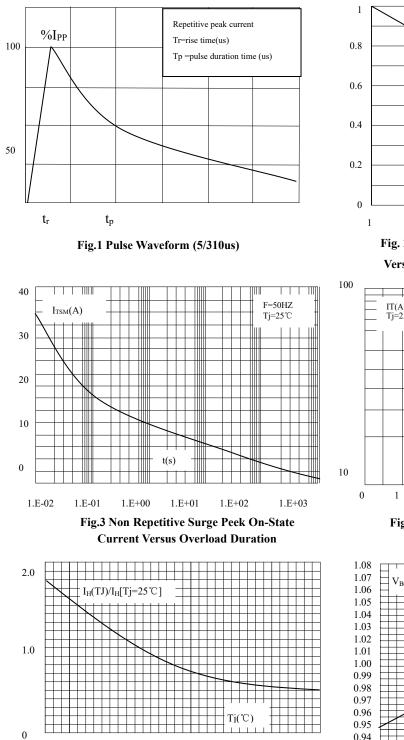
• Absolute maximum rating @TA=25°C

Symbol	Parameter	Value	Units	
		10/1000 us	100	
I_{PP}	Non-repetitive peak pulse current	5/310 us	150	А
		8/20 us	400	
V _{PP}	Non-repetitive peak pulse voltage 10/700us		6000	V
	ESD Rating per IEC61000-4-2:		0	
V _{ESD}	V _{ESD} Contact		8	KV
	Air		15	
Ts	Storage temperature range		-40 to +150	°C
Tj	Maximum junction temperature		150	°C

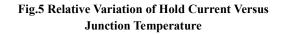
• Electrical Characteristics @TA=25°C

	VRM	IRM	Vво	Іво	VT	IT	Со	I _H
Туре	Min.	Max.		Max.	Max.		Тур.	Тур.
	V	μA	V	mA	V	Α	pF	mA
TQTHDB326V 0	6	5	25	800	4	2.2	100	50





• Typical Performance Characteristics



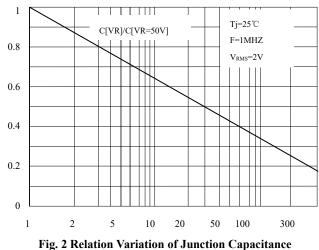
80

60

100

120

130





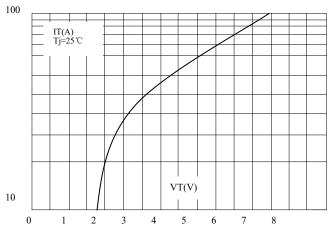


Fig.4 On-State Voltage Versus On-State Current (Typical Values)

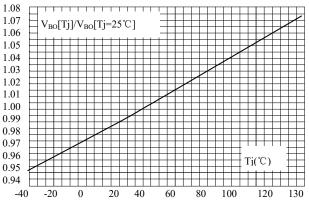


Fig.6 Relative Variation of Break Over Voltage Versus Junction Temperature

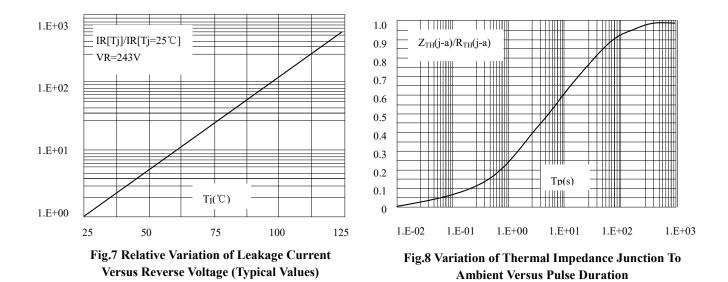
-20

-40

0

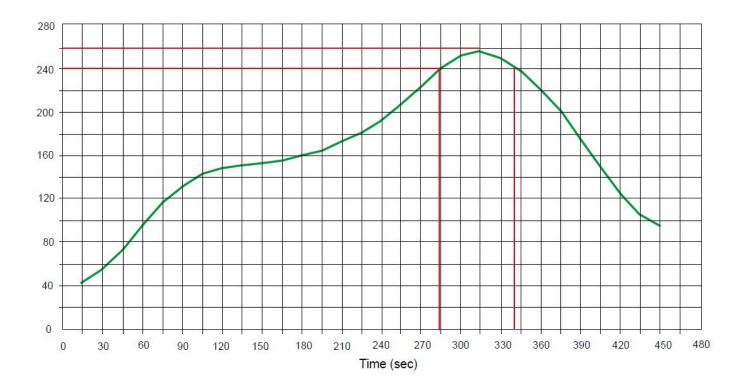
20 40





• Solder Reflow Recommendation

Peak Temp=257°C, Ramp Rate=0.802deg. °C/sec





• PackageInformation

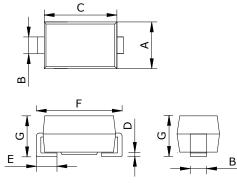
Ordering Information

Device	Marking	Package	Qty per Reel	Reel Size
TQTHDB326V0	P008C	SMB	2500	13 Inch

Mechanical Data

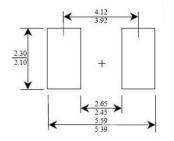
Case:SMB

Case Material: Molded Plastic. UL Flammability



DIM	Millimeters				
	Min	Nom	Max		
A	3.30	3.60	3.94		
В	1.80	2.00	2.21		
С	4.05	4.45	5.30		
D	0.051	0.20	0.203		
E	0.76	1.14	1.52		
F	5.08	5.25	5.59		
G	2.05	2.30	2.45		

Recommended Pad outline



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